

iscN-Channel MOSFET Transistor

TK8A45D

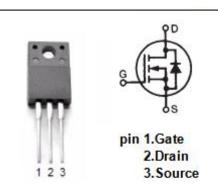
• FEATURES

- Low drain-source on-resistance: $R_{DS}(ON) = 0.9\Omega$ (MAX)
- · Enhancement mode:
 - Vth = 2.4 to 4.4V (VDs = 10 V, ID=1.0mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)



TO-220F package

mm

MAX

10.10

4.60

0.90

3.30

3.90

0.70

13.6

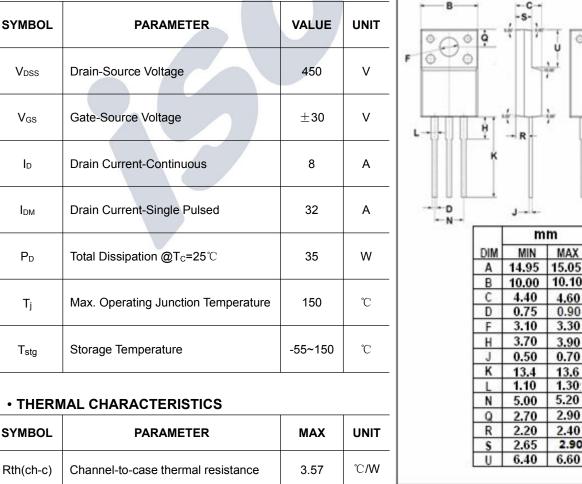
1.30 5.20

2.90

2.40

2.90

6.60



1

isc website: www.iscsemi.cn



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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 10mA	450			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} = 10V; I _D =1.0mA	2.4		4.4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =4A			0.9	Ω
lgss	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} = 0V			±1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =450V; V _{GS} = 0V			10	μA
V _{SDF}	Diode forward voltage	I _{DR} =8A, V _{GS} = 0 V			1.7	V



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2